

## 650V, 40A, Trench FS III Fast IGBT

### General Description

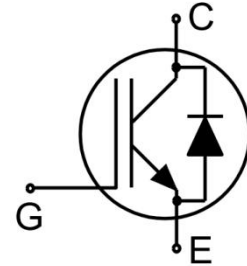
Using NCE's proprietary trench design and advanced FS (Field Stop) second generation technology, the 650V Trench FS III IGBT offers superior conduction and switching performances, and easy parallel operation;

### Features

- Trench FSIII Technology offering
- Very low  $V_{CE(sat)}$
- High speed switching
- Positive temperature coefficient in  $V_{CE(sat)}$
- Very tight parameter distribution
- High ruggedness, temperature stable behavior

### Application

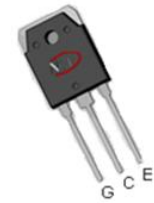
- Air Condition
- Inverters
- Motor drives



Schematic diagram

### Package Marking and Ordering Information

Device	Device Package	Device Marking
NCE40ER65BP	TO-3P	NCE40ER65BP



TO-3P

### Absolute Maximum Ratings ( $T_C=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
$V_{CES}$	Collector-Emitter Voltage	650	V
$V_{GES}$	Gate- Emitter Voltage	$\pm 30$	V
$I_C$	Collector Current	80	A
	Collector Current @ $T_C = 100^{\circ}\text{C}$	40	A
$I_{Cpuls}$	Pulsed Collector Current, $t_p$ limited by $T_{jmax}$	120	A
-	Turn off safe operating area, $V_{CE}=650\text{V}$ , $T_J=175^{\circ}\text{C}$	120	A
$I_F$	Diode Continuous Forward Current @ $T_C = 100^{\circ}\text{C}$	40	A
$I_{FM}$	Diode Maximum Forward Current	120	A
$P_D$	Power Dissipation @ $T_C = 25^{\circ}\text{C}$	245	W
	Power Dissipation @ $T_C = 100^{\circ}\text{C}$	122.5	W
$T_J, T_{stg}$	Operating Junction and Storage Temperature Range	-55 to +175	$^{\circ}\text{C}$
$T_L$	Maximum Temperature for Soldering	260	$^{\circ}\text{C}$

**Thermal Characteristic**

Symbol	Parameter	Value	Units
$R_{\theta JC}$	Thermal Resistance, Junction to case for IGBT	0.61	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction to case for Diode	2.00	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	40	°C/W

**Electrical Characteristics ( $T_C=25^\circ\text{C}$  unless otherwise noted)**

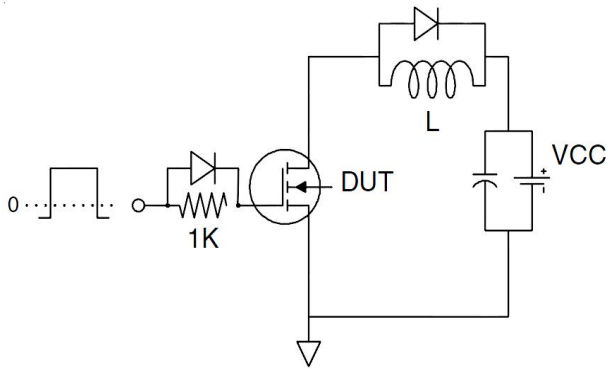
Symbol	Parameter	Conditions	Value			Units	
			Min.	Typ.	Max.		
<b>Static Characteristics</b>							
$V_{(BR)CES}$	Collector-Emitter Breakdown Voltage	$V_{GE}=0V, I_{CE}=1mA$	650	--	--	V	
$I_{CES}$	Collector-Emitter Leakage Current	$V_{GE}=0V, V_{CE}=650V$	--	--	40	$\mu A$	
$I_{GES(F)}$	Gate to Emitter Forward Leakage	$V_{GE}=+30V, V_{CE}=0V$	--	--	200	nA	
$I_{GES(R)}$	Gate to Emitter Reverse Leakage	$V_{GE}=-30V, V_{CE}=0V$	--	--	200	nA	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=40A$	--	$T_J=25^\circ\text{C}$	1.40	1.75	V
		$V_{GE}=15V$		$T_J=175^\circ\text{C}$	1.75	--	V
$V_{GE(th)}$	Gate Threshold Voltage	$I_C=1mA, V_{CE}=V_{GE}$	4.0	5.0	6.0	V	
<b>Dynamic Characteristics</b>							
$C_{ies}$	Input Capacitance	$V_{CE}=25V, V_{GE}=0V,$ $f=1MHz$	--	1365	--	pF	
$C_{oes}$	Output Capacitance		--	54	--		
$C_{res}$	Reverse Transfer Capacitance		--	12	--		
$Q_g$	Total Gate Charge	$V_{CC}=480V, I_C=40A,$ $V_{GE}=15V$	--	57	--	nC	
$Q_{ge}$	Gate to Emitter Charge		--	5	--		
$Q_{gc}$	Gate to Collector Charge		--	28	--		
<b>Switching Characteristics</b>							
$t_{d(ON)}$	Turn-on Delay Time	$V_{CC}=400V, I_C=40A,$ $V_{GE}=0/15V, R_g=5\Omega,$ Inductive Load	--	18	--	ns	
$t_r$	Rise Time		--	16	--		
$t_{d(OFF)}$	Turn-Off Delay Time		--	169	--		
$t_f$	Fall Time		--	15	--		
$E_{on}$	Turn-On Switching Loss		--	0.60	--	mJ	
$E_{off}$	Turn-Off Switching Loss			0.47	--		
$E_{ts}$	Total Switching Loss			1.07	--		
$E_{on}$	Turn-On Switching Loss		$V_{CC}=400V, I_C=40A,$ $V_{GE}=0/15V, R_g=5\Omega,$ $T_J=175^\circ\text{C}$	--	0.75	--	mJ
$E_{off}$	Turn-Off Switching Loss			--	0.68	--	
$E_{ts}$	Total Switching Loss	--		1.43	--		

**Electrical Characteristics of the Diode ( $T_c = 25^\circ\text{C}$  unless otherwise specified)**

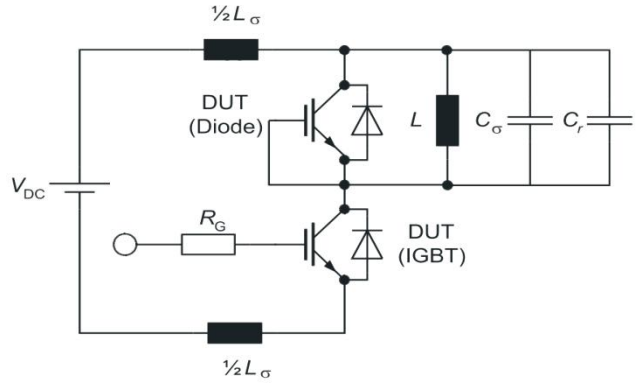
Symbol	Parameter	Conditions	Rating			Units
			Min.	Typ.	Max.	
$V_{FM}$	Diode Forward Voltage	$I_F = 40\text{A}$	--	2.2	2.8	V
$T_{rr}$	Reverse Recovery Time	$I_F = 40\text{A}$ , $di/dt = 200\text{A}/\mu\text{s}$	--	244	--	ns
$I_{RRM}$	Diode Peak Reverse Recovery Current		--	3.8	--	A
$Q_{rr}$	Reverse Recovery Charge		--	0.45	--	$\mu\text{C}$
$T_{rr}$	Reverse Recovery Time	$I_F = 40\text{A}$ , $di/dt = 200\text{A}/\mu\text{s}$ , $T_j = 175^\circ\text{C}$	--	450	--	ns
$I_{RRM}$	Diode Peak Reverse Recovery Current		--	5.6	--	A
$Q_{rr}$	Reverse Recovery Charge		--	1.22	--	$\mu\text{C}$

Test Circuit

1) Gate Charge Test Circuit

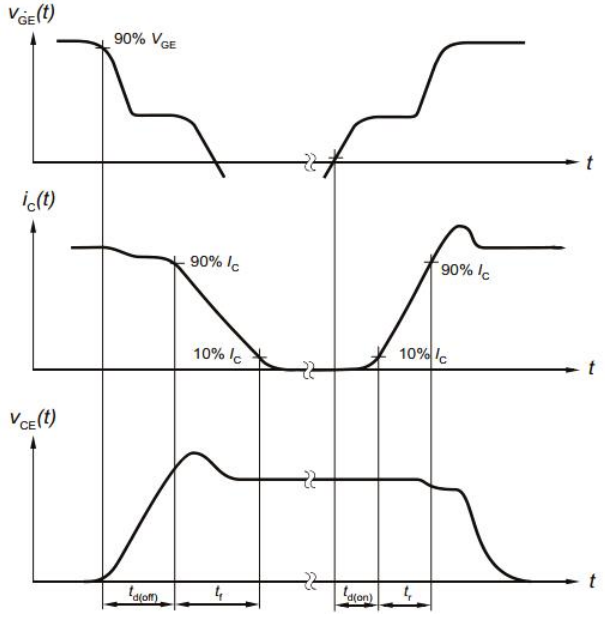


2) Switch Time Test Circuit

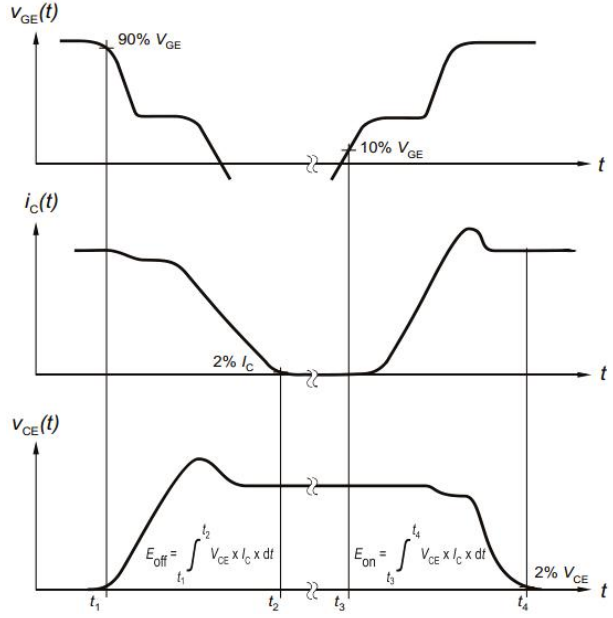


Switching characteristics

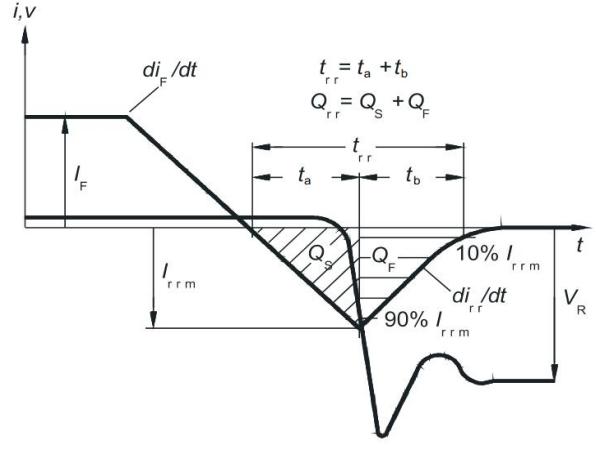
1) Definition of switching times



2) Definition of switching losses



3) Definition of diode switching characteristics



Typical Electrical and Thermal Characteristics

Figure 1 Output Characteristics

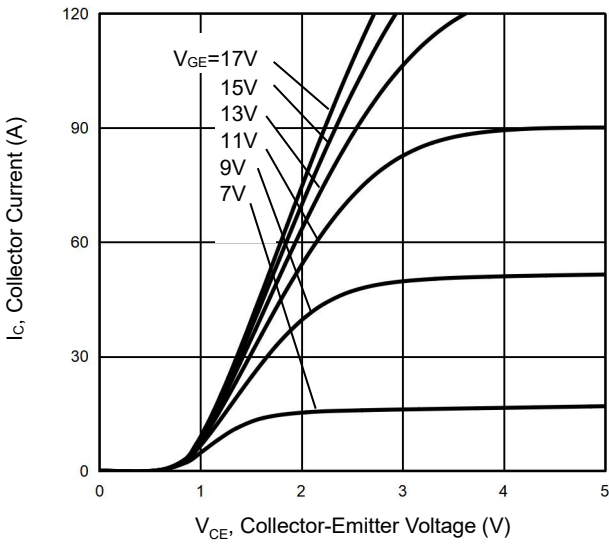


Figure 2 Transfer Characteristics

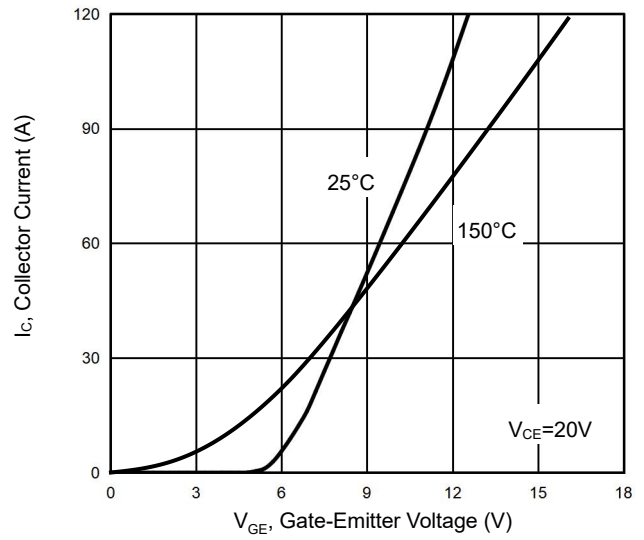


Figure 3  $V_{CE(sat)}$  vs. Temperature

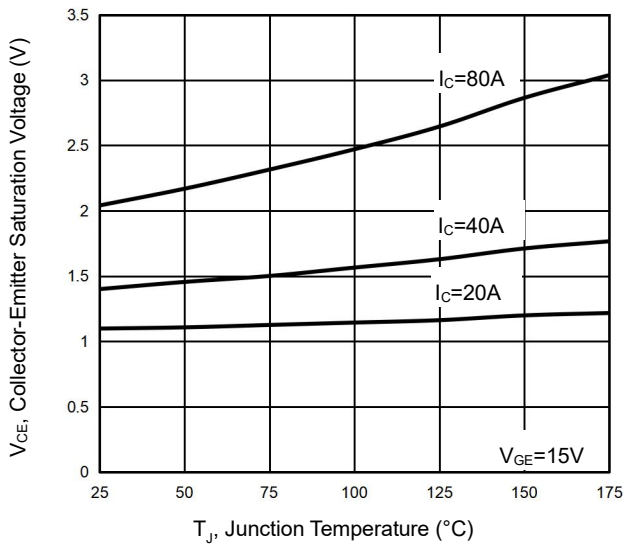


Figure 4 Saturation Voltage vs.  $V_{GE}$

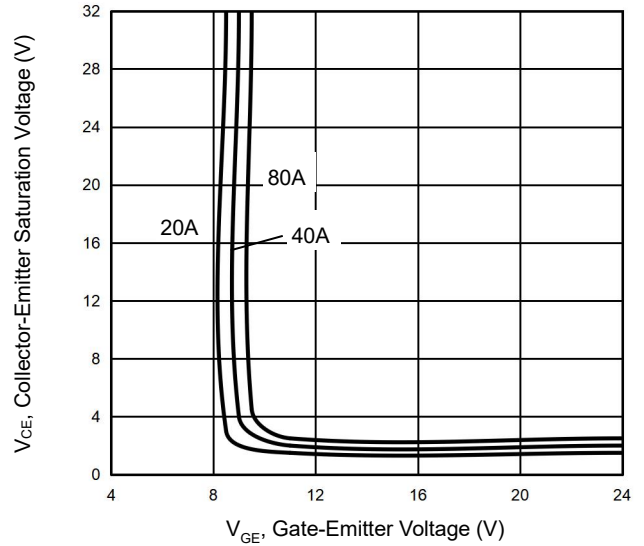


Figure 5 Capacitance Characteristics

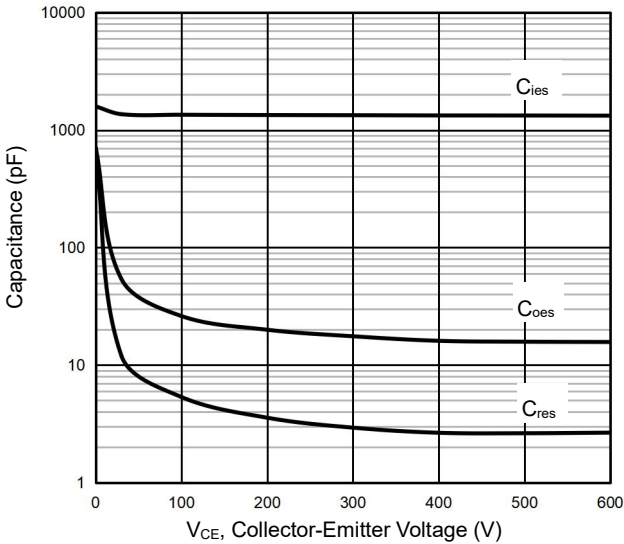
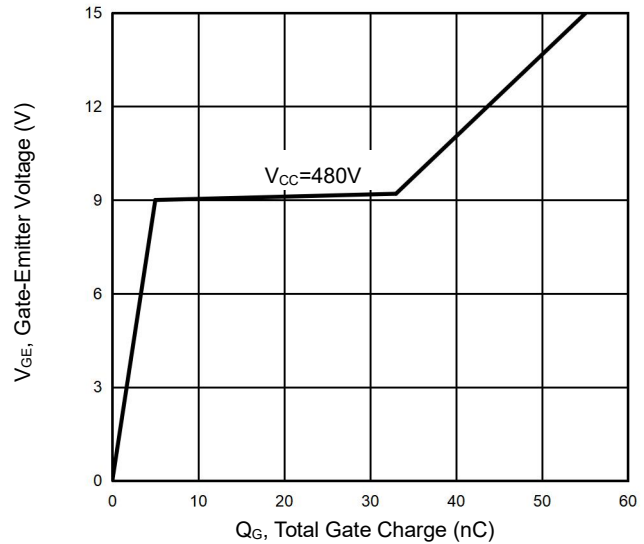


Figure 6 Gate Charge Wave Form



Typical Electrical and Thermal Characteristics

Figure 7 Forward Characteristics

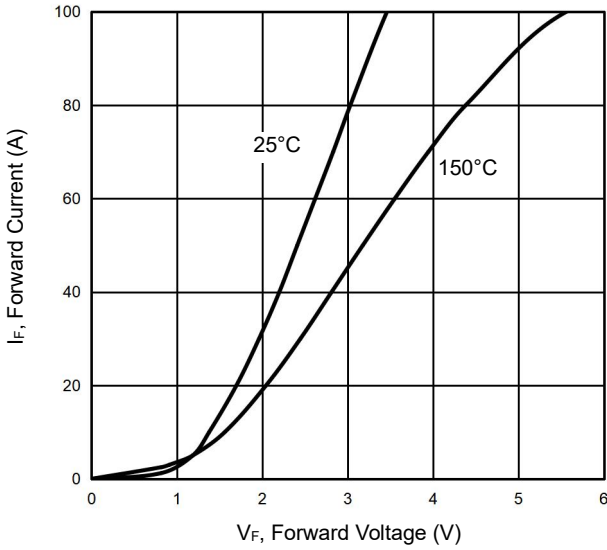


Figure 8  $V_F$  vs. Temperature

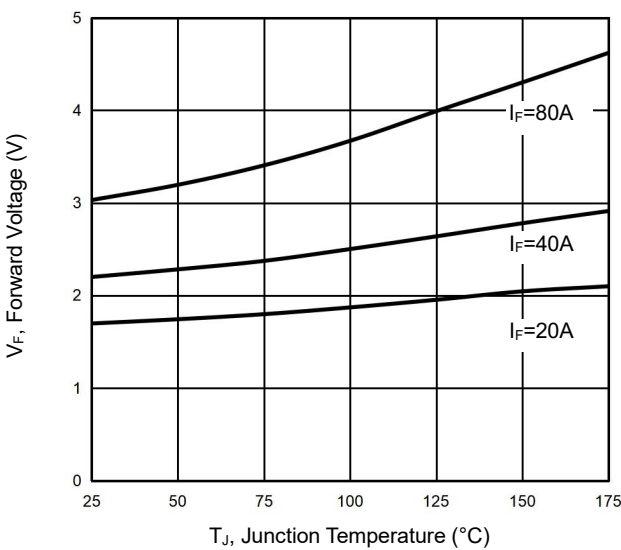


Figure 9 Switching Loss vs.  $R_G$

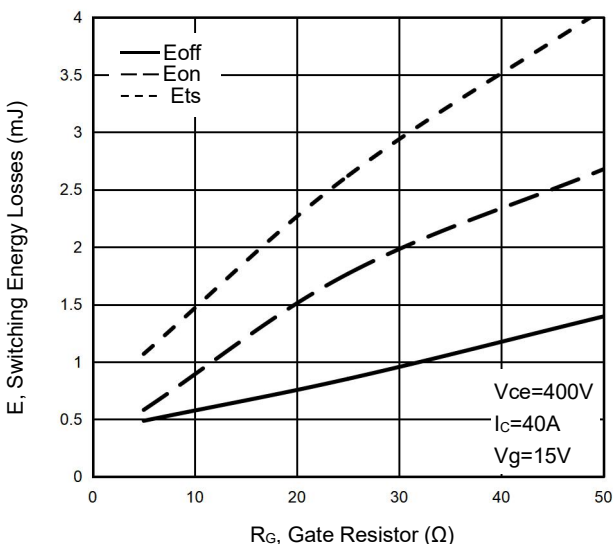


Figure 10 Switching Energy vs. Temperature

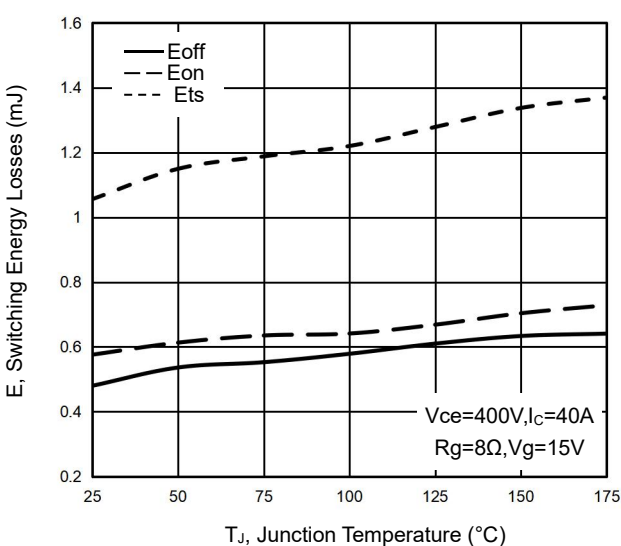


Figure 11 Switching Loss vs. Collector Current

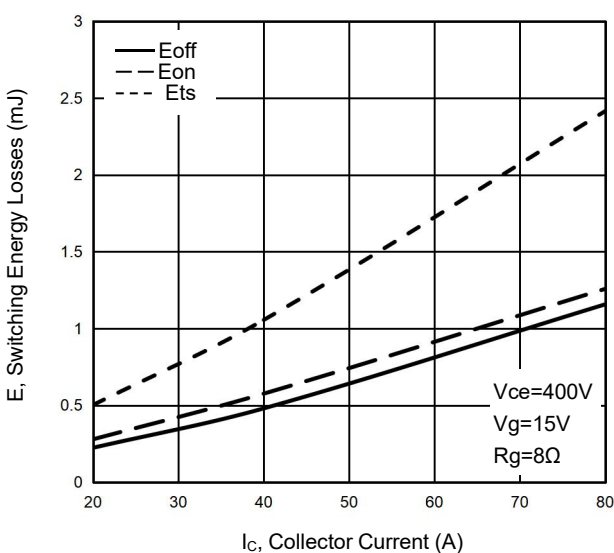
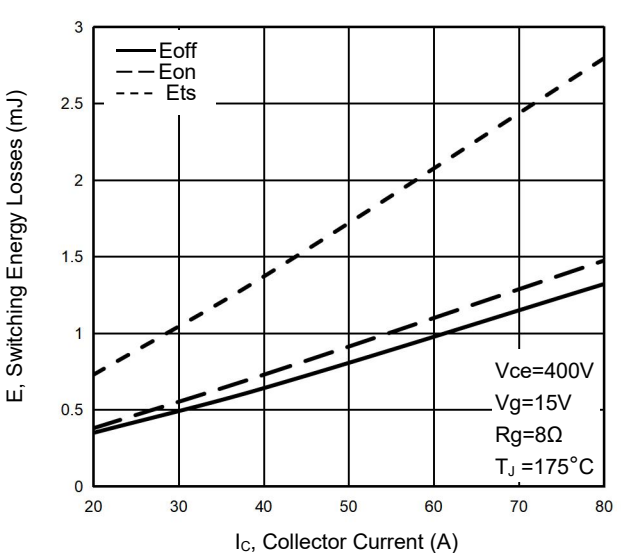
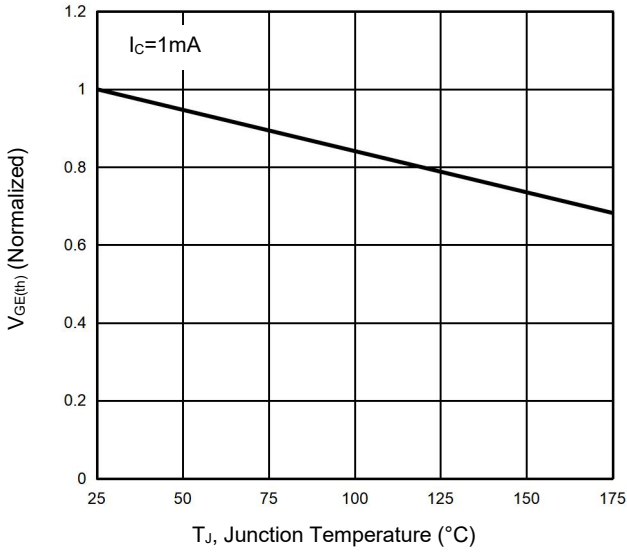


Figure 12 Switching Loss vs. Collector Current

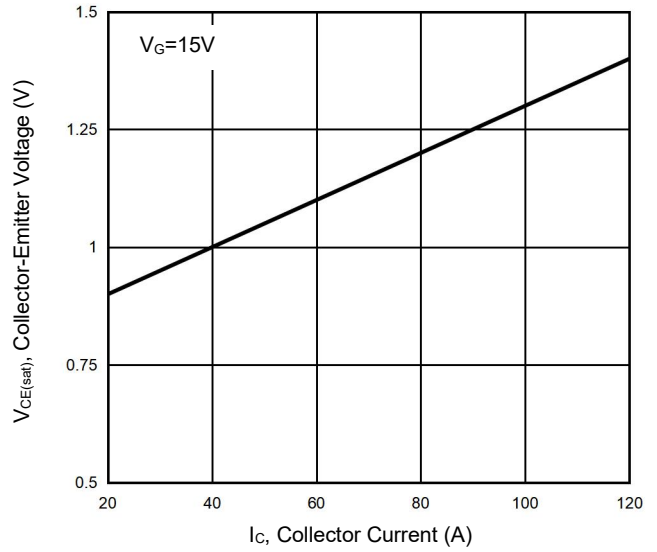


## Typical Electrical and Thermal Characteristics

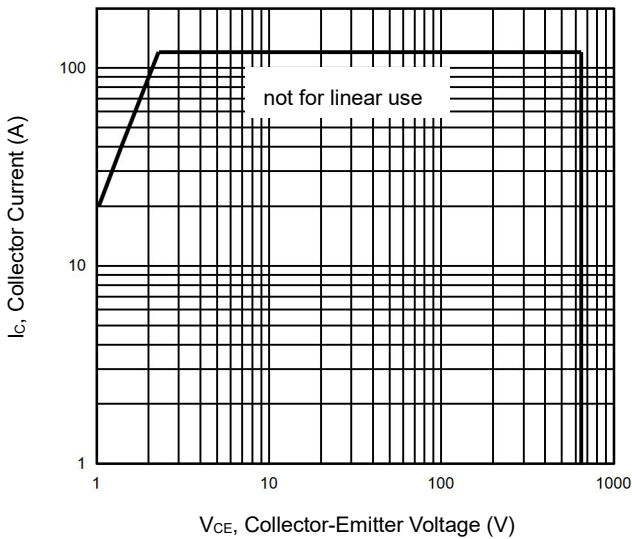
**Figure 13  $V_{GE(th)}$  vs. Junction Temperature**



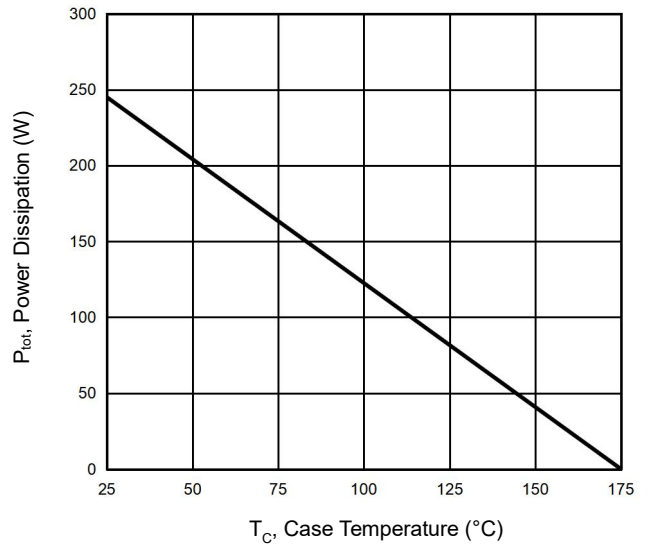
**Figure 14  $V_{CE(SAT)}$  vs. Collector Current**



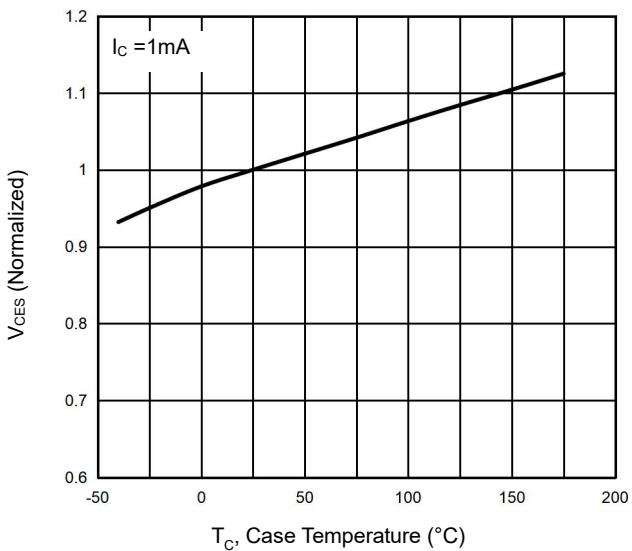
**Figure 15 Forward Bias Safe Operating Area**



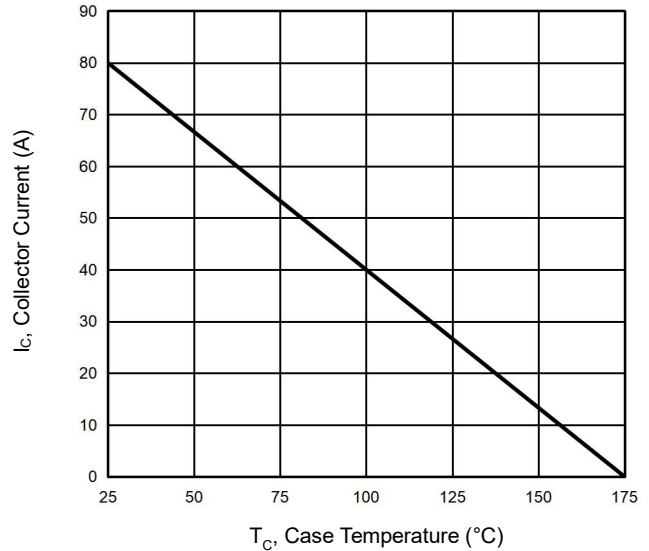
**Figure 16  $P_{tot}$  vs. Case Temperature**



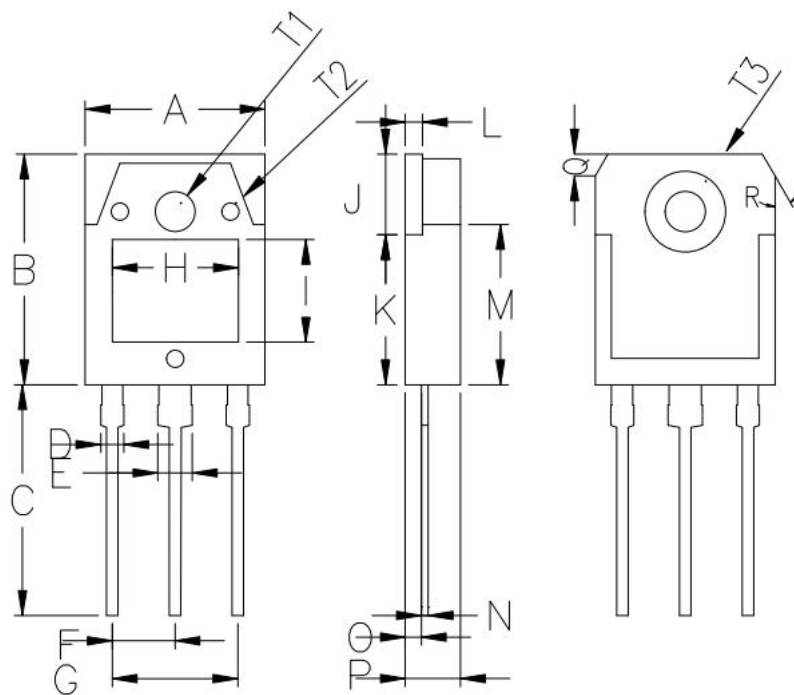
**Figure 17  $V_{CES}$  vs. Temperature**



**Figure 18  $I_C$  vs. Temperature**



## TO-3P-S Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	15.50	15.70	0.61	0.62
B	19.70	20.10	0.78	0.79
C	20.10	20.50	0.79	0.81
D	2.00		0.08	
E	3.00		0.12	
F	5.45		0.21	
G	10.90		0.43	
H	10.80	11.00	0.43	0.43
I	8.80	9.00	0.35	0.35
J	6.85	7.15	0.27	0.28
K	12.75	13.05	0.50	0.51
L	1.49	1.51	0.06	0.06
M	13.70	14.00	0.54	0.55
N	0.59	0.61	0.02	0.02
O	1.32	1.48	0.05	0.06
P	4.70	4.90	0.19	0.19
Q	1.90	2.10	0.07	0.08
R	30°		1.18°	
S	4°		0.16°	
T1	3.50		0.14	
T2	1.50		0.06	
T3	7.00		0.28	



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